AlGaAs/InGaAs Power P-HEMTs for High-Efficiency, Low-Voltage Portable Applications

M.J. Martinez, E. Schirmann, M. Durlam, J.-H. Huang, S. Tehrani, N. Cody, T. Driver and K. Barkley. "AlGaAs/InGaAs Power P-HEMTs for High-Efficiency, Low-Voltage Portable Applications." 1996 MTT-S International Microwave Symposium Digest 96.2 (1996 Vol. II [MWSYM]): 551-554.

Power Pseudomorphic High Electron Mobility Transistors (P-HEMTs) with unprecedented efficiency are being produced for low-voltage portable wireless products. 12-mm devices operating at 3.5 achieve more than 75% power added efficiency, 1.5 W output power, and 11.5 dB gain, simultaneously, at a frequency of 850 MHz.

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